

HM50256 Series

262144-word × 1-bit Dynamic Random Access Memory

FEATURES

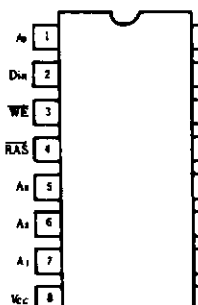
- Industry Standard 16-Pin DIP, 18-Pin PLCC, 16-Pin ZIP
- Single 5V ($\pm 10\%$)
- On chip substrate bias generator
- Low Power: 350mW active, 20mW standby
- High speed: Access Time 120ns/150ns/200ns(max.)
- Common I/O capability using early write operation
- Page mode capability
- TTL compatible
- 256 refresh cycles $\dots$ (4ms)
- 3 variations of refresh $\dots$ $\overline{RAS}$ only refresh, $\overline{CAS}$ before $\overline{RAS}$ refresh, Hidden refresh

ORDERING INFORMATION

Type No.	Access Time	Package
HM50256P-12	120ns	300 mil 16 pin Plastic DIP
HM50256P-15	150ns	
HM50256P-20	200ns	
HM50256ZP-12	120ns	16 pin Plastic ZIP
HM50256ZP-15	150ns	
HM50256ZP-20	200ns	
HM50256CP-12	120ns	18 pin PLCC
HM50256CP-15	150ns	
HM50256CP-20	200ns	

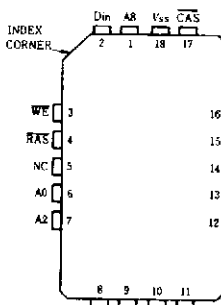
PIN ARRANGEMENT

HM50256P Series



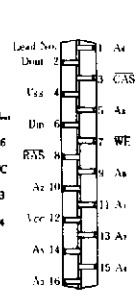
(Top View)

HM50256CP Series



(Top View)

HM50256ZP Series



(Bottom View)

HM50256P Series



(DP-16B)

HM50256CP Series



(CP-18)

HM50256ZP Series



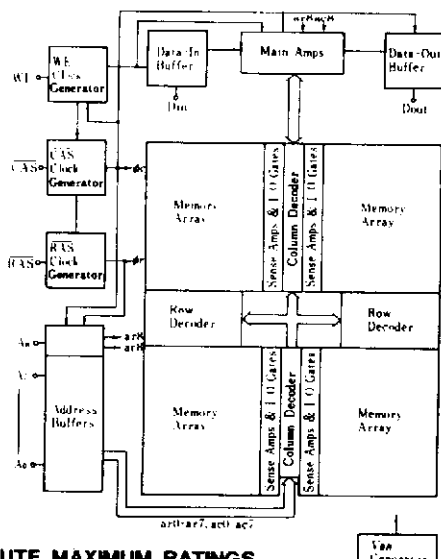
(ZP-16)

PIN DESCRIPTION

A ₀ - A ₇	Address Inputs
CAS	Column Address Strobe
Din	Data In
Dout	Data Out
RAS	Row Address Strobe
WE	Read/Write Input
V _{cc}	Power (+5V)
V _{ss}	Ground
A ₈ - A ₉	Refresh Address Inputs



■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Voltage on any pin relative to V_{SS} -1V to +7V
 Operating temperature, T_a (Ambient) 0°C to +70°C
 Storage temperature -55°C to +125°C
 Short circuit output current 50mA
 Power dissipation 1W

■ RECOMMENDED DC OPERATING CONDITIONS ($T_a = 0$ to +70°C)

Parameter	Symbol	min	typ	max	Unit	Note
Supply Voltage	V_{CC}	4.5	5.0	5.5	V	1
Input High Voltage	V_{IH}	2.4	—	6.5	V	1
Input Low Voltage	V_{IL}	-1.0	—	0.8	V	1

Note) 1. All voltages referenced to V_{SS}

■ DC ELECTRICAL CHARACTERISTICS ($T_a = 0$ to +70°C, $V_{CC} = 5V \pm 10\%$, $V_{SS} = 0V$)

Parameter	Symbol	HM50256-12		HM50256-15		HM50256-20		Unit	Notes
		min	max	min	max	min	max		
Operating Current(RAS, CAS = Cycling; $t_{RC} = \min$)	I_{CC1}	—	83	—	70	—	55	mA	1
Standby Current(RAS = V_{IH} , Dout = High Impedance)	I_{CC2}	—	4.5	—	4.5	—	4.5	mA	
Refresh Current(RAS only Refresh, $t_{RC} = \min$)	I_{CC3}	—	62	—	53	—	42	mA	
Standby Current(RAS = V_{IH} , Dout = Enable)	I_{CC4}	—	10	—	10	—	10	mA	1
Refresh Current(CAS before RAS Refresh, $t_{RC} = \min$)	I_{CC5}	—	69	—	58	—	45	mA	
Page Mode Supply Current(RAS = V_{IL} , CAS = Cycling, $t_{RC} = \min$)	I_{CC6}	—	57	—	48	—	37	mA	
Input leakage($0 < V_{in} < 7V$)	I_{IL}	-10	10	-10	10	-10	10	μA	
Output leakage($0 < V_{out} < 7V$, Dout = Disable)	I_{LO}	-10	10	-10	10	-10	10	μA	
Output levels High($I_{OH} = -5mA$)	V_{OH}	2.4	V_{CC}	2.4	V_{CC}	2.4	V_{CC}	V	
Output levels Low($I_{OL} = 4.2mA$)	V_{OL}	0	0.4	0	0.4	0	0.4	V	

Notes) 1. I_{CC} depends on output loading condition when the device is selected. I_{CC} max is specified at the output open condition.



■ CAPACITANCE ($V_{CC} = 5V \pm 10\%$, $T_a = 25^\circ C$)

Parameter	Symbol	typ	max	Unit	Notes
Input Capacitance	Address, Data-in	C_{in}	—	5	1
	Clocks	C_{in}	—	7	1, 2
Output Capacitance	Data-out	C_o	—	7	1, 2

Notes) 1. Capacitance measured with Boonton Meter or effective capacitance measuring method.
 2. CAS = V_{in} to disable Dout.

■ ELECTRICAL CHARACTERISTICS AND RECOMMENDED AC OPERATING CONDITIONS

($T_a = 0$ to $+70^\circ C$, $V_{CC} = 5V \pm 10\%$, $V_{SS} = 0V$) ^{1), 10), 11)}

Parameter	Symbol	HM50256-12		HM50256-15		HM50256-20		Unit	Notes
		min	max	min	max	min	max		
Random Read or Write Cycle Time	t_{RC}	220	—	260	—	330	—	ns	
Read-Write Cycle Time	t_{RWC}	265	—	310	—	390	—	ns	
RAS to CAS Delay Time	t_{RCD}	25	60	25	75	30	100	ns	7
Access Time from RAS	t_{RAC}	—	120	—	150	—	200	ns	2, 3
Access Time from CAS	t_{CAC}	—	60	—	75	—	100	ns	3, 4
Output Buffer Turn-off Delay	t_{OFF}	—	30	—	40	—	50	ns	5
Transition Time (Rise and Fall)	t_T	3	50	3	50	3	50	ns	6
RAS Precharge Time	t_{RP}	90	—	100	—	120	—	ns	
RAS Pulse Width	t_{RAS}	120	10000	150	10000	200	10000	ns	
RAS Hold Time	t_{RSH}	60	—	75	—	100	—	ns	
CAS Hold Time	t_{CSH}	120	—	150	—	200	—	ns	
CAS Pulse Width	t_{CAS}	60	10000	75	10000	100	10000	ns	
CAS to RAS Precharge Time	t_{CRP}	10	—	10	—	10	—	ns	
Row Address Set-up Time	t_{ASR}	0	—	0	—	0	—	ns	
Row Address Hold Time	t_{RAH}	15	—	15	—	20	—	ns	
Column Address Set-up Time	t_{ASC}	0	—	0	—	0	—	ns	
Column Address Hold Time	t_{ACH}	20	—	25	—	30	—	ns	
Column Address Hold Time referenced to RAS	t_{AH}	80	—	100	—	130	—	ns	
Read Command Set-up Time	t_{RCS}	0	—	0	—	0	—	ns	
Read Command Hold Time referenced to CAS	t_{RCH}	0	—	0	—	0	—	ns	
Write Command Set-up Time	t_{WCS}	0	—	0	—	0	—	ns	8
Write Command Hold Time	t_{WCH}	40	—	45	—	55	—	ns	
Write Command Hold Time referenced to RAS	t_{WCR}	100	—	120	—	155	—	ns	
Write Command Pulse Width	t_{WP}	40	—	45	—	55	—	ns	
Write Command to RAS Lead Time	t_{RWL}	40	—	45	—	55	—	ns	
Write Command to CAS Lead Time	t_{RWS}	40	—	45	—	55	—	ns	
Data-in Set-up Time	t_{DIS}	0	—	0	—	0	—	ns	9
Data-in Hold Time	t_{DIH}	40	—	45	—	55	—	ns	8, 9
Data-in Hold Time referenced to RAS	t_{DIHR}	100	—	120	—	155	—	ns	
RAS to WE Delay	t_{RWD}	120	—	150	—	200	—	ns	
CAS to WE Delay	t_{CWD}	60	—	75	—	100	—	ns	8
Page Mode Read or Write Cycle	t_{RC}	120	—	145	—	190	—	ns	
Page Mode Read Modify Write Cycle	t_{RCM}	165	—	195	—	250	—	ns	
CAS Precharge Time, Page Cycle	t_{CP}	50	—	60	—	80	—	ns	
Read Command Hold Time referenced to RAS	t_{RHR}	10	—	10	—	10	—	ns	
Refresh Period	t_{REF}	—	4	—	4	—	4	ms	
CAS Set-up Time	t_{CSR}	10	—	10	—	10	—	ns	
CAS Hold Time (CAS before RAS Refresh)	t_{CHR}	120	—	150	—	200	—	ns	
RAS Precharge to CAS Hold Time	t_{RPC}	0	—	0	—	0	—	ns	

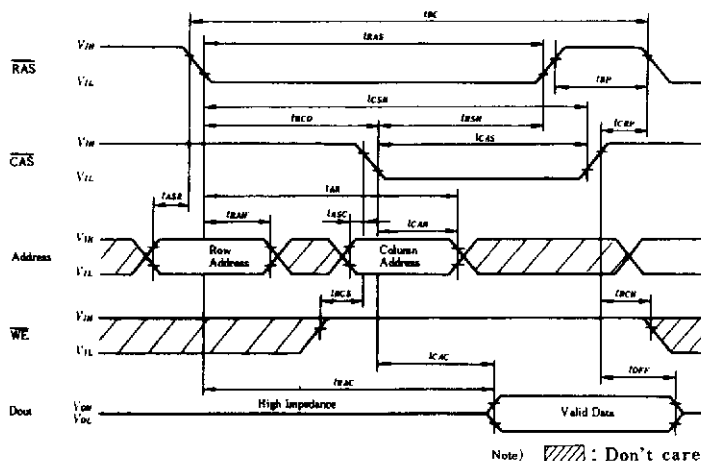


Notes

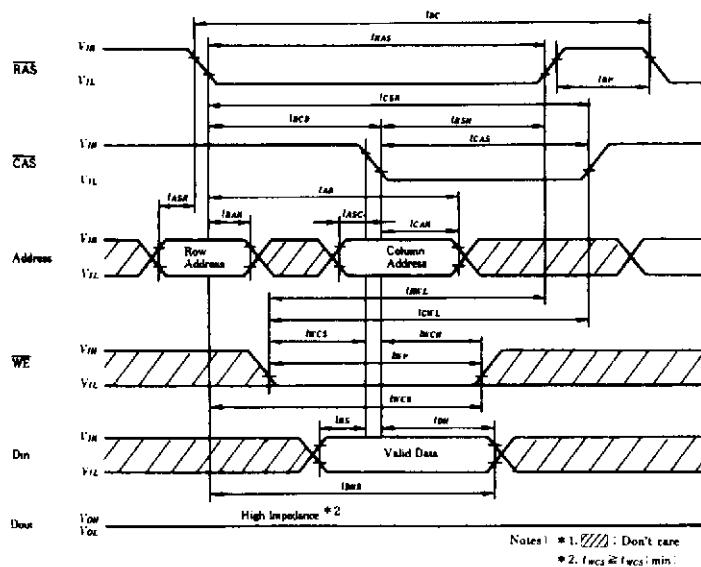
1. AC measurements assume $t_T = 5\text{ns}$.
2. Assumes that $t_{RCD} \leq t_{RCD}(\text{max})$. If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAC} exceeds the value shown.
3. Measured with a load circuit equivalent to 2TTL loads and 100pF.
4. Assumes that $t_{RCD} \geq t_{RCD}(\text{max})$.
5. $t_{OFF}(\text{max})$ is defined as the time at which the output achieves the open circuit condition and output voltage levels are not referred.
6. $V_{IH}(\text{min})$ and $V_{IL}(\text{max})$ are reference levels for measuring timing of input signals. Also, transition times are measured between V_{IH} and V_{IL} .
7. Operation with the $t_{RCD}(\text{max})$ limit insures that $t_{RAC}(\text{max})$ can be met, $t_{RCD}(\text{max})$ is specified as a reference point only; if t_{RCD} is greater than the specified $t_{RCD}(\text{max})$ limit, access time is controlled exclusively by t_{CAC} .
8. t_{WCS} , t_{CWD} and t_{RWD} are not restrictive operating parameters. They are included in the data sheet as electrical characteristics only; if $t_{WCS} \geq t_{WCS}(\text{min})$, the cycle is an early write cycle and the data output pin will remain open circuit (high impedance) throughout the entire cycle; if $t_{CWD} \geq t_{CWD}(\text{min})$ and $t_{RWD} \geq t_{RWD}(\text{min})$, the cycle is a read-write and the data output will contain data read from the selected cell; if neither of the above sets of conditions is satisfied the condition of the data out (at access time) is indeterminate.
9. These parameters are referenced to $\overline{\text{CAS}}$ leading edge in early write cycles and to $\overline{\text{WE}}$ leading edge in delayed write or read-modify-write cycles.
10. An initial pause of 100 μs is required after power-up then execute at least 8 initialization cycles.
11. At least, 8 $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh cycles are required before using internal refresh counter.

TIMING WAVEFORMS

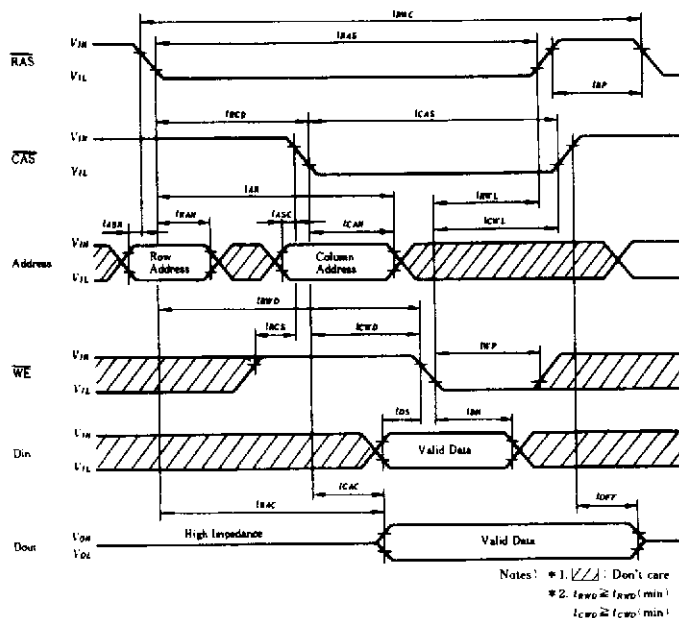
READ CYCLE

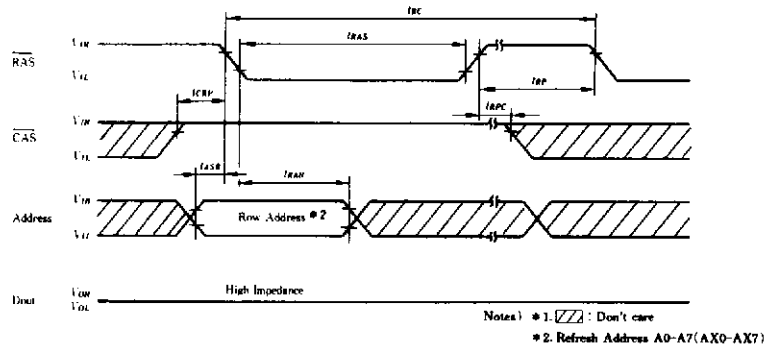


● WRITE CYCLE

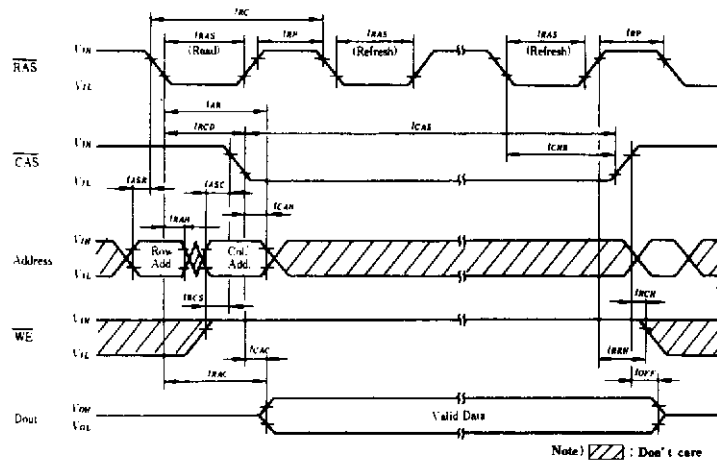


● READ MODIFY WRITE CYCLE



● $\overline{\text{RAS}}$ ONLY REFRESH CYCLE

● HIDDEN REFRESH CYCLE

● $\overline{\text{CAS}}$ BEFORE $\overline{\text{RAS}}$ REFRESH CYCLE